L Number	Hits	Search Text	DB	Time stamp
1	489	garnet.ab.	USPAT	2003/04/04
				16:46
2	86	garnet.ab. and semiconductor	USPAT	2003/04/04
				16:55
3	0	(garnet.ab. and semiconductor) and 'm.sub.3 al.sub.5. o.sub.12'	USPAT	2003/04/04 16:47
4	0	'm.sub.3 al.sub.5. o.sub.12'	USPAT	2003/04/04
	U	111.8ub.3 al.sub.3. 0.8ub.12	OSIAI	16:47
5	0	'm.sub.3 al.sub.5 o.sub.12'	USPAT	2003/04/04
				16:47
6	16	'Re.sub.3 al.sub.5 o.sub.12'	USPAT	2003/04/04
				16:47
7	75	(garnet.ab. and semiconductor) and (coating or layer or film)	USPAT	2003/04/04
				17:11
8	0	garnet.ab. and 'reactive chamber'	USPAT	2003/04/04
9	0	garnet.ab. and 'etch reactor'	USPAT	17:12 2003/04/04
9	U	garnet.ab. and eten reactor	USPAI	17:12
l 10	0	garnet.ab. and 'turbine rotor'	USPAT	2003/04/04
	_	8		17:13
11	15	garnet.ab. and halogen	USPAT	2003/04/04
				17:20
12	7	garnet.ab. and (wafer with silicon)	USPAT	2003/04/04
,,	4		* 10D 4 T	17:22
13	4	Gobain and garnet	USPAT	2003/04/04 17:23
14	0	simpson.in. and garnet	USPAT	2003/04/04
1'	O	Simpson.in. and garnet	OSIAI	17:24
15	0	billieres.in. and garnet	USPAT	2003/04/04
				17:24
16	0	main.in. and garnet	USPAT	2003/04/04
l				17:24
17	0	drouin.in. and garnet	USPAT	2003/04/04
10	7	gamet alm and 'thomal angu'	LICDAT	17:25
18	7	garnet.clm. and 'thermal spray'	USPAT	2003/04/04 17:29
19	255	garnet and semiconductor	EPO; JPO;	2003/04/04
	255	1 Description	DERWENT	17:29
20	157	(garnet and semiconductor) and (film or coating or layer)	EPO; JPO;	2003/04/04
	•		DERWENT	17:30